I hereby certify that this correspondence is being deposited via first class mail with the United States Postal Service addressed to: Commissioner of Patents and Trademarks, Alexandria, VA 22313, on February 22, 2005. The applicant and/or attorney requests the date of deposit as the filing date. Depositor: Nicole Barrese

Recel Barrise 2/22:05

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In recapplication of :

February 22, 2005

Deris, et al.

Group Art Unit:

Serial No: 10/707,018

Examiner:

Filed: 11/14/03

International Business Machines Corporation

2070 Route 52

Hopewell Junction, NY 12533

TITLE: Stressed Semiconductor Device Structures Having Granular Semiconductor Material

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the US and non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or nonpertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,

Doris, et al.

Joseph P. Abate

Registration No. 30,238

Telephone No. 845-894-4633

5-82-35

FORM PTO	-14	49 (Modified)	7 6 70 05 8		ATTY. DOCKET NO. F1S920030189US1		SERIAL NO. 10/707,018		
LIST OF PA APPLICAN STATEMEN	rs	INTS AND PUBLICATION DIS	TIONS FOR		APPLICANT: Doris, et al.				
(Use several	she	eets if necessary)			FILING DATE: 11/14/03		GROUP:		
REFERENCE	DI	ESIGNATION	U.S.	PATE	ENT DOCUMENTS				
EXAMINER INITIALS		DOCUMENT NUMBER	DATE		NAME	CLASS	S SUBCLASS	FILING DATE (IF APPRO.)	
a car meater	<u></u>	6,228,694 B1	5/8/2001		Doyle et al.				
		6,406,973 B1	6/18/2002		Lee				
		6,281,532 B1	8/28/2001		Doyle et al.				
		5,683,934	11/4/97		Candelaria			· 	
		6,368,931 B1	4/9/2002		Kuhn, et al.	<u>· </u>			
		5,310,446	5/10/94		Konishi et al.			·	
		4,853,076	8/1/89		Tsaur et al.			<u> </u>	
		US 2002/0090791 A1	7/11/2002		Doyle et al.			•	
US 200	US 2002/0074598 A1	6/20/2002		Doyle et al.					
		6,509,618 B2	B2 1/21/2003		Jan et al.			•	
		6,476,462 B2	11/5/2002		Shimizu et al.				
	_	6,362,082 B1	3/26/2002		Doyle et al.				
		6,228,694 B1	5/8/2001		Doyle et al.				
		5,565,697	10/15/96		Asakawa et al.				
		US 2003/0040158 / A1	2/27/2003	<u> </u>	Saitoh				
	╝	US 2002/0086472 √ A1	7/4/2002		Roberds et al.			·	
	_	6,521,964 B1	2/18/2003		Jan et al.	·			
		6,506,652	01/14/03		Jan, et al.	<u></u>			
			FOREIG	N PA	TENT DOCUMENTS	• .			
		DOCUMENT NUMBER	DATE		COUNTRY	CLASS	SUBCLASS	RANSLATION YES NO	
	لــِـ	OTHER	ART (Includin	g Auth	or, Title, Date, Pertine	nt Pages, etc	.)		
								•	
XAMINER	1				DATE CONSIDERE	D ·	•	•	

DILE FEB # 8 3005 FORM PTO-1449 (Modified) ATTY. DOCKET NO. SERIAL NO. 10/707,018 FIS920030189US1 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT: APPLICANT'S INFORMATION DISCLOSURE Doris, et al. **STATEMENT** GROUP: (Use several sheets if necessary) FILING DATE: 11/14/03 REFERENCE DESIGNATION **U.S. PATENT DOCUMENTS EXAMINER DOCUMENT FILING DATE** INITIALS DATE **SUBCLASS** NUMBER **NAME CLASS** (IF APPRO.) 5,081,513 1/14/1992 Jackson, et al. 3,602,841 8/31/1971 McGroddy 6,531,740 3/11/2003 Bosco, et al. 6,531,369 3/11/2003 Ozkan, et al. 6,501,121 12/31/2002 Yu, et al. 6,498,358 12/24/2002 Lach, et al. 6,493,497 12/10/2002 Ramdani, et al. 6,403,975 6/11/2002 Brunner, et al. 6,361,885 3/26/2002 Chou 6,255,169 7/3/2001 Li, et al. 6/12/2001 6,246,095 Brady, et al. 6,165,383 12/26/2000 Chou 10/17/2000 6,133,071 Nagai 6,046,464 4/4/2000 Schetzina 6,025,280 2/15/2000 Brady, et al. FOREIGN PATENT DOCUMENTS DOCUMENT TRANSLATION NUMBER DATE **COUNTRY** SUBCLASS **CLASS** YES NO OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) EXAMINER DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-14		FEB 9 8 7005 H	ATTY. DOCKET NO. FIS920030189US1		SERIAL NO. 10/707,018			
APPLICANTS	INFORMATION DI	SCLOSURE S	APPLICANT:					
STATEMENT		VIA DEMO	Doris, et al.					
(Use several she	eets if necessary)		FILING DATE: 11/14/03		GROUP:			
REFERENCE DI	ESIGNATION	U.S. P.	ATENT DOCUMENTS		_			
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLAS	FILING I		
	5,940,736	8/17/1999	Brady, et al.				10.,	
	5,880,040	3/9/1999	Sun, et al.			1		
	5,861,651	1/19/1999	Brasen, et al.		- -	 		
	5,679,965	10/21/1997	Schetzina			 		
	5,670,798	9/23/1997	Schetzina					
	5,561,302	10/1/1996	Candelaria			 		
	5,471,948	12/5/1995	Burroughes, et al.					
	5,459,346	10/17/1995	Asakawa, et al.			 		
	5,391,510	2/21/1995	Hsu, et al.			 		
	5,371,399	12/6/1994	Burroughes, et al.					
	5,108,843	4/28/1992	Ohtaka, et al.	<u> </u>	 		•	
	5,060,030	10/22/1991	Hoke			 		
· i	4,958,213	9/18/1990	Eklund, et al.			<u> </u>		
	4,665,415	5/12/1987	Esaki, et al.		 			
	6,635,506	10/21/2003	Volant et al.					
		FOREIGN	PATENT DOCUMENTS	-		<u> </u>		
	DOCUMENT					TRANSLAT		
	NUMBER	DATE	COUNTRY	CLASS	SUBCLASS		NO	
	ОТНЕ	R ART (Including A	Author, Title, Date, Pertinent	Pages etc	•			
		(The same of the sa	1 11603) 010	·/			
i_i		· · · · · · · · · · · · · · · · · · ·						
XAMINER		DATE CONSIDERED						
YAMNED: Initi	al if reference consid	and whather or no	t citation is in conformance wi	1 1 000000 6				

	49 (Modified) मह	斑	ATTY. DOCKET NO	I i			SERIAL NO. 10/707,018		
APPLICANT'S STATEMENT	NTS AND PUBLICA INFORMATION DI	ATIONS FOR SCLOSURE	APPLICANT: Doris, et al.						
(Use several she	ets if necessary)		FILING DATE: 11/14/03		GROUP:				
REFERENCE DE	ESIGNATION	U.S.	PATENT DOCUMENTS						
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLAS		G DAT PPRO.)		
	5,989,978	11/23/1999	Peidous						
	6,284,626	9/4/2001	Kim						
	6,274,444	8/14/2001	Wang						
	6,261,964	7/17/2001	Wu, et al.						
	6,221,735	4/24/2001	Manley, et al.						
	6,117,722	9/12/2000	Wuu, et al.				_		
	6,107,143	8/22/2000	Park, et al.						
	6,090,684	7/18/2000	Ishitsuka, et al.						
	6,066,545	5/23/2000	Doshi, et al.						
	6,008,126	12/28/1999	Leedy						
	5,946,559	8/31/1999	Leedy		·				
	5,840,593	11/24/1998	Leedy						
	5,592,018	1/7/1997	Leedy						
	5,592,007	1/7/1997	Leedy						
	5,571,741	11/5/1996	Leedy						
		FOREIG	N PATENT DOCUMENTS						
	DOCUMENT					TRANSI	ATION		
	NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO		
	ОТНЕК	R ART Ancluding	g Author, Title, Date, Pertine	nt Panae ata	1				
			, , , , , , , , , , , , , , , , , , , ,	11 1 ages, etc	·/	<u> </u>			
KAMINER			DATE CONSIDERE	D					
XAMINER: Initi	al if reference consid	ered whether or	not citation is in conformance v	with MDED 4	00 D	thuesest			
ot in conformance	and not considered.	Include copy of the	his form with next communication	tion to applica	ant.	en onâu c	ication i		

LIST OF PATE	H49 (Modified) HE ENTS AND PUBLICA INFORMATION DIS	TIONS FOR	FIS920030189US1 APPLICANT:	APPLICANT:				
STATEMENT Class several share	eets if necessary)		Doris, et al.					
(Ose several she	eets if necessary)		FILING DATE: 11/14/03					
REFERENCE DI	ESIGNATION	U.S.	PATENT DOCUMENTS					
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DAT (IF APPRO.)		
	5,557,122	9/17/1996	Shrivastava, et al.					
	5,354,695	10/11/1994	Leedy					
	5,134,085	7/28/1992	Gilgen, et al.					
	5,006,913	4/9/1991	Sugahara, et al.					
	4,952,524	8/28/1990	Lee, et al.					
	4,855,245	8/8/1989	Neppl, et al.					
	2002/0086497	07-04-2002	Kwok					
	5,960,297	09-28-1999	Saki					
	6,403,486	06-11-2002	Lou					
	6,284,623	09-04-2001	Zhang et al.			-		
	2003/0032261	02-13-2003	Yeh et al.					
	2003/0057184	03-27-2003	Yu et al.					
	6,265,317	07-24-2001	Chiu et al.					
	2003/0067035	04-10-2003	Tews et al.					
	6,461,936	10-08-2002	von Ehrenwall			· · · · · · · · · · · · · · · · · · ·		
	6,319,794	11-20-2001	Akatsu et al.					
	2001/0009784	07-26-2001	Ma et al.					
	6,621,392	09-16-2003	Volant et al.					
		FOREIG	N PATENT DOCUMENTS					
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SIBCLASS	RANSLATION YES NO		
	OTHER	ART (Including	Author, Title, Date, Pertine	ent Pages, etc	•	: ::0		
			· · · · · · · · · · · · · · · · · · ·		-			
XAMINER			DATE CONSIDERE	ED				

Docket Number (Optional) Application Number FIS920030189US1 10/707,018 INFORMATION DISCLOSURE CITATION Applicant(s) (Use several sheets if necessary) Doris, et al. FEB TO Group Art Unit rilling Date 11/14/03 U.S. PATENT DOCUMENTS EXAMINER NAME CLASS FILING DATE DOCUMENT NUMBER DATE SUBCLASS REF ENTTEAL SF APPROPRIATE 8/17/1999 5,940,716 Jin, et al. 6,483,171 B1 Forbes, et al. 11/19/02 2002/0063292 A1 5/30/02 Armstrong, et al. FOREIGN PATENT DOCUMENTS DATE COUNTRY CLASS SUBCLASS DOCUMENT NUMBER NO 03-1989 Japan JP64-76755 OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) DATE CONSIDERED **EXAMINER** EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

	FORM PTO-1449 (Mo ENTS AND PUBLICA S INFORMATION EM	ATTY. DOCKET NO. FIS920030189US1 APPLICANT: Doris, et al.	FIS920030189US1 10/707,018 APPLICANT:				
(Use several sh	¥.<2	eth James J	FILING DATE: GROUP:				
REFERENCE D	DESIGNATION	U.S.	PATENT DOCUMENTS		_		
EXAMINER INITIALS	DOCUMENT NUMBER	DATE			SUBCLASS	FILING DATE (IF APPRO.)	
		FOREI	GN PATENT DOCUMENTS				
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO	
	ОТНЕ	ART (Includin	ng Author, Title, Date, Pertinen	it Pages, etc	:.)		
	Kern Rim, et al., 'International Elec	Transconductation Devices M	ance Enhancement in Deep Soleeting, 26, 8, 1, IEEE, Septer	ubmicron S nber 1998.	Strained-Si n-M	OSFETs",	
	Kern Rim, et al., '	'Characteristics	s and Device Design of Sub-10 mology Digest of Technical Pa	00 nm Stra	ined Si N- and	PMOSFETs*,	
	Gregory Scott, et	al., "NMOS Dri	ive Current Reduction Caused ational Electron Devices Meet	by Transis	stor Lavout and	Trench	
	F. Ootsuka, et al.	, "A Highly Den	se, High-Performance 130nm tion", International Electron D	node CMC	OS Technology	for Large	
	Shinya Ito, et al., Transistor Design	"Mechanical St ", International	ress Effect of Etch-Stop Nitrid Electron Devices Meeting, 10	e and its In	npact on Deep April 2000.	Submicron	
	A. Shimizu, et al.,	"Local Mechar	nical-Stress Control (LMC): A loctron Devices Meeting, IEEE,	New Techr	nique for CMOS	S-Performance	
-	K. Ota, et al., "No	vel Locally Stra	ined Channel Technique for heeting, 2.2.1, IEEE, February	igh Perforr		MOS*,	
XAMINER			DATE CONSIDERED				
KAMINER: In	itial if reference considered.	ered, whether or Include copy of	not citation is in conformance withis form with next communication	ith MPEP 60	09. Draw line thant.	rough citation if	

	INFO	RMATION DISCLOSURE	CYNTION	Sign of the second	Pocket Number (Optional FIS920030189US1 Applicant(s)		Application Numbe	r	
		(Use severai sneets ij necessa	of the James	OFFICE OF	Doris, et al. Filing Date	· ·	Group Art Unit		
			U.S.		11/14/03 DOCUMENTS		L		
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	U.S.	OFF.	NAME	CLASS	SUBCLASS	1	IG DATE
								<u>,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,</u>	COLKETE
					···				-
- 41	-								
				-			_		
			U.S. PATENT	APPLICA	TION PUBLICATION	s			
*EXAMINER INITIAL REF DOCUMENT NUMBER DATE NAME		CLASS	SUBCLASS		G DATE COPRIATE				
				_				<u></u>	
					· · · · · · · · · · · · · · · · · · ·				
			FOREIC	GN PATE	NT DOCUMENTS	<u> </u>			
	REF	DOCUMENT NUMBER	DATE		COUNTRY	CLASS	SUBCLASS	Tran YES	station NO
							-		
				· · · ·	•				
				-				· · · · · · · · · · · · · · · · · · ·	
			OTHER D	DCUMEN	TS (Including A	uthor, Title, Date, I	Pertînent Pages, E	(e) ·	
	i	G. Zhang, J. Cressler, G SiGe Bipolar Transistors	Niu, A. Joseph, ". IEEE Transa:	'A New '	Mixed-Mode' Reliabil Electron Devices, vol.	lity Degradation 49, no. 12, Dece	Mechanism in A nber 2002, pp. 2	dvanced S 151-56.	Si and
		H.S. Momose, Y. Niitsu, its Mechanism Analyzed	H. Iwai, K. Maeg by MOS Structu	uchi, "Te res". Pap	mperature Dependen er 6.2, pp. 140-143.	ce of Emitter-Ba	se Reverse Stres	s Degrada	tion and
					A ATT CANOTE TO				
EXAMINE					DATE CONSIDERED				
EXAMINE not conside	R: Initi red. In	al if citation considered, whether o clude copy of this form with next c	or not citation is in communication to a	conforman	ce with MPEP Section 6	09; Draw line thro	ugh citation if not	in conform	nance and
				9004	/BEV/05	Detect and Trades	nark Office * U.S. DEP	ARTMENT OF	COMMERCE

*					Docket Number (Ontional	\	Analisadan N		
						•	Application Numb	čr	
	INFO	RMATION DISCLOSURA (Use several sheets if neaess)	CTTATION		FIS920030189US1 Applicant(s)		10//0/,018		
		(Use several sheets if necessi	(c)	77 //	Doris, et al Filing Date				
		A ₁ .	LEH SE SUITE	13 13 13 13 13 13 13 13 13 13 13 13 13 1			Group Art Unit		
			1100	~	<u>11</u> /14/03				
		fā.	, us	PATENT	DOCUMENTS				
*EXAMINER	REF	DOCUMENT NUMBER	DATE		NAME OF THE PARTY			FILI	NG DATE
INITIAL	KL	DOCUMENT NUMBER	DATE		NAME	CLASS	SUBCLASS	1	ROPRIATE
	İ .								
								├	
								1	
		· · · · · · · · · · · · · · · · · · ·					 	1	
		·						<u> </u>	
. •		\$				•			
								 	
						1	į	İ	
			IIS PATENT	ADDI ICA	TION PUBLICATIONS				
	_		T I	ATTLICA		, , , , , , , , , , , , , , , , , , ,	·		
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE		NAME	CLASS	SUBCLASS	ł	G DATE
-				· · · · · · · · · · · · · · · · · · ·	-			IF APPR	OPRIATE
			ł						
			 						
			1 1			İ	l		
			<u> </u>						
			FOREI	GN PATEN	T DOCUMENTS				
	REF	DOCUMENT NUMBER	DATE	-	COUNTRY	CLASS	SUBCLASS	Translation	
							SUBCIASS	YES	NO
			ĺ			ŀ			
-			 						
			ļ						
							•		
	Ì								
					 				
			OTHER DO	CUMENT	S · (Including Au	thor, Title, Date, P	ertinent Pages, Et	c.)	į
	Ī	CJ. Huang, CJ. Sun, T. Degradation Effects in B	A. Grotjohn, D.K.	. Reinhard	"Temperature Depe	endence and Pos	-Stress Recover	y of Hot H	lectron
		Degradation Effects in B	ipolar Transistors	s". IEEE	1991 Bipolar Circuits	and Technology	Meeting 7.5, p	». 170-173.	•
	╬	S.R. Sheng, S.P. McAllis	ter, J.P. McCaffro	ey, S. Kova	icic, "Degradation an	d Recovery of Si	Ge HBTs Folio	wing Radi	ation and
	į	Hot-Carrier Stressing".	Pp. 14-15.		, -				
	1								
			·····						
EXAMINEI	R			11	DATE CONSIDERED	•			
		l if citation considered, whether o			with MPEP Section 60	9; Draw line throu	gh citation if not	in conform	ance and
not consider	ea. Inc	lude copy of this form with next co	ommunication to ap	plicant.					
Form PTO-	ARON			P09A/R	EV05	Patent and Tradem	rk Office * U.S. DEP/	ARTMENT OF	COMMERCE

•					Docket Number (Optional)	Application Numb	er	
ŀ	TATEO	DRMATION DISCLOSUE	STEE.	•	FIS920030189US1		10/707,018		
	INFO	RMATION DISCLOSUF Use several sheets if neces	CE/CEYATION		Applicant(s)				
		(Ose several sneets ly neces	1	. 8	Doris, et al. Filing Date		Group Art Unit		
			FEB 7 5 200		11/14/03		Group Art Cart		
				S STEET	r DOCUMENTS				
	,		V .		DOCUMENTS				
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE		NAME	CLASS	SUBCLASS	1	NG DATE
	i		1						MURICAL
	 							 	
				l		1	ı	1	
				 				 	
٠.		•	•••	į					
								 	
								ļ	
			IIC DATES	F A DDV 10				<u></u>	
	r		U.S. PATEN	APPLICA	ATION PUBLICATIONS	; 			
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	Ì	NAME	CLASS	SUBCLASS	FILING DATE	
		· · · · · · · · · · · · · · · · · · ·	1					IF APPI	ROPRIATE
							1	ĺ	
				_					
								ļ	
						Ì			
								 	
								<u> </u>	
			FOREI	GN PATE	NT DOCUMENTS				
									
	REF	DOCUMENT NUMBER	DATE		COUNTRY	CLASS	SUBCLASS	YES	estation NO
	1								
									ļ
į.			İ			i e		! 	ļ
			ļ		·				<u> </u>
İ						İ			1
			+				 		
							1		ļ
			OTHER D	DCUMENT	S (Including Aut	hor, Title, Date, Pe	rtinenî Pages. Ete	٤)	
	7	Z. Yang, F. Gaurin, E. I Heterojunction Bipolar	Hostetter, G. Freer	nan, "Avı			-		Ge
	i	Heterojunction Bipolar	Transistors". Pp.	1-5.					
	ł								
		H. Li. H.M. Rein, T. Sui	ttorn, "Design of V	V-Band V	COs with High Output	Day ar for Pota	tia) Application	- (- 77 C)	· ·
	j	H. Li, H.M. Rein, T. Su Automotive Radar Syste	ems". 2003 TEEE	CaAs Dig	est, pp. 263-266.	ower for role	idei Appucatio	am ii Vi	nz
EXAMINER	l .				DATE CONSIDERED				
·		· · · · · · · · · · · · · · · · · · ·		f			<u> </u>		
XAMINER	: Initial	if citation considered, whether	or not citation is in c	onformanc	e with MPEP Section 609	; Draw line throug	h citation if not i	n conform	ance and
ot consider	ed. Incl	ude copy of this form with next o	communication to ap	plicant.					
orm PTO-/	1000			PAGAA	REV05	Patent and Tradema	·		

	INFO	RMATION DISCLOSUR	ECITATION	Docket Number (Ontional) FIS920030189US1 Applicant(s)		Application Number 10/707,018	:	
		(Use several sheets if/neces:	sary) 🤗	Doris, et al.				
		()	EB 700 B B	Filing Date		Group Art Unit		
		₹%	ω	11/14/03				
		Eq.	. Vis.	PATENT DOCUMENTS				
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	1	IG DATE ROPRIATE
							 	
			1	-			 	
			_11			l		
			U.S. PATENT	APPLICATION PUBLICATIONS				·
"EXAMINER ENITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS		G DATE
							IFAPPR	OPRIATE
			-					
				·····				
			FOREIC	GN PATENT DOCUMENTS	-			
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS SUBCLASS		Tran	sintion
			 				YES	NO
					İ			
				· · · · · · · · · · · · · · · · · · ·				
			 	· · · · · · · · · · · · · · · · · · ·				
				·				
			OTHER DO	CUMENIS (Including Auth	or, Title, Date, Po	ertinent Pages, Etc	: .)	
		H. Wurzer, R. Mahnko	pf, H. Klose, "Anne	caling of Degraded npn-Transisto no. 4, April 1994, pp. 533-538.	rs-Mechanism	s and Modeling	". IFEF:	
		Transactions on Electro	ni Devices, voi. 41,	им 4, арги 1994, рр. 333-336.				
		B. Doyle, G.J. Dunn, "F	Recovery of Hot-Ca	rrier Damage in Reoxidized Nitri 3-40.	ided Oxide MO	SFET's". IEEI	E Electron	Device
	ĺ	Letters, vol. 13, no. 1, J	andary 1992, pp. 38	→4v.				
EXAMINE	₹			DATE CONSIDERED				
		l if citation considered, whether lude copy of this form with next		onformance with MPEP Section 609; plicant.	Draw line throu	gh citation if not	in conform	ance and
				DOGA/DCI/DS				

		DRMATION DISCLOSUR	ECTTATION		Docket Number (Optional) FIS920030189US1 Applicant(s)		Application Numb	er	
		(Use several sheets if necess	ary) 👸		Doris, et al. FWing Date		C		
			FEB 7 8 7005		11/14/03		Group Art Unit		
		N. C. C. C. C. C. C. C. C. C. C. C. C. C.	U.S	PATEN	T DOCUMENTS				
•EXAMINER INITIAL	REF	DOCUMENT NUMBER	E MITE ME		NAME	CLASS	SUBCLASS	1	NG DATE PROPRIATE
									KUIKIKIE
								 	
								 	
			-	<u> </u>				 	
	<u> </u>		U.S. PATENT	APPLIC	ATION PUBLICATIONS			<u> </u>	
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE		NAME	CLASS	Julius		IG DATE
			FOREIG	EN PATE	NT DOCUMENTS				
	REF	DOCUMENT NUMBER	DATE	<u>.</u>	COUNTRY	CLASS	SUBCLASS	Tran	station NO
			OTHER DO	CUMEN	IS (Including Aut)	hor, Title, Date, Pe	rtinent Pages, Etc	<u>-</u>	1
		H.S. Momose, H. Iwal, " Transistors for Bi-CMOS	Analysis of the Ter S". IEEE Transac	mperatu tions on	re Dependence of Hot-C Electron Devices, vol. 4	arrier-Induced 1, no. 6, June 19	Degradation in 1994, pp. 978-987	Bipolar	
	į				1				
EXAMINER					DATE CONSIDERED				
EXAMINER of consider	: Initial	if citation considered, whether or ude copy of this form with next co	not citation is in communication to see	nformano	e with MPEP Section 609	; Draw line throug	h citation if not i	n conform	ance and